	Hits	Search Text	DBs
1	2	micromachin$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and (passivat$9 same conformal$6) and ((etch$4 same passivat$6) same 9alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (time or second or minute)) and (passivat$4 same (time or second or minute)) and undercut$4 and (alter$4 same (passivat$4 or etch$4 same undercut$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	2	micromachin$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and (passivat$9 same conformal$6) and ((etch$4 same passivat$6) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (time or second or minute)) and (passivat$4 same (time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
3	24	(("5198390") or ("5199917") or ("5235187") or ("5287082") or ("5316979") or ("5363021") or ("5375033") or ("5393375") or ("5399415") or ("5436070") or ("5449903") or ("5506175") or ("5546988") or ("5563343") or ("5610335") or ("5627427") or ("5628917") or ("5637539") or ("5640133") or ("5846849") or ("5847454") or ("5501893") or ("5498312") or ("5856722")).PN.	US-PGPUB; USPAT
4	2	micromachin$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and passivat$9 and conformal$6 and (((etch$4 or RIE) same passivat$6) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (rate or time or second or minute)) and (passivat$4 same (rate or time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	2	micromachin$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and (SiO$2 or passivat$9 or (thermal$3 near9 oxid$5)) and conformal$6 and (((etch$4 or RIE) same (oxidi$6 or passivat$6)) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (rate or time or second or minute)) and ((SiO$3 or (thermal$4 near9 oxid$6) or passivat$4) same (rate or time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	2	micromachin$4 and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and (SiO$2 or passivat$9 or (thermal$3 near9 oxid$5)) and (((etch$4 or RIE) same (oxidi$6 or passivat$6)) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (rate or time or second or minute)) and ((SiO$3 or (thermal$4 near9 oxid$6) or passivat$4) same (rate or time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
7	2	(micromachin$4 or (micro near4 mechan$5)) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE) same undercut$4) and (etch$4 same isotropic$6) and (SiO$2 or passivat$9 or (thermal$3 near9 oxid$5)) and (((etch$4 or RIE) same (oxidi$6 or passivat$6)) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (rate or time or second or minute)) and ((SiO$3 or (thermal$4 near9 oxid$6) or passivat$4) same (rate or time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	45	(micromachin$4 or (micro near4 mechan$5)) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE)) and (etch$4 same isotropic$6) and (SiO$2 or passivat$9 or (thermal$3 near9 oxid$5)) and (((etch$4 or RIE) same (oxidi$6 or passivat$6)) same (alternat$4 or subsequent$4 or simultaneous$5)) and (etch$4 near16 (rate or time or second or minute)) and ((SiO$3 or (thermal$4 near9 oxid$6) or passivat$4) same (rate or time or second or minute)) and undercut$4 and (release near9 structure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	0	(micromachin$4 or (micro near8 mechan$5) or MEMS) and ((substrate or wafer or carrier or workpiece) same (mask or pattern) same (resist or photoresist or photosensitive) same (etch$4 or RIE)) and (etch$4 same isotropic$6) and (SiO$2 or passivat$9 or (thermal$3 near9 oxid$5)) and (((etch$4 or RIE) same (oxidi$6 or passivat$6)) same (alternat$4 or subsequent$4 or simultaneous$5)) and ((SiO$3 or (thermal$4 near9 oxid$6) or passivat$4) same (rate or time or second or minute)) and undercut$4 and ((first near14 release near9 structure) same (underly$4 or (self$4align$4) or beneath or bottom) same (second near12 release near9 structure) same (different or vary$4 or non$4uniform) same (topograph$4 or width or breadth or diameter or dimension$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB